

Field Effect Transistor

Silicon P Channel MOS Type (L²-π-MOS IV)

High Speed, High Current DC-DC Converter,

Relay Drive and Motor Drive Applications

Features

- 4-Volt Gate Drive
- Low Drain-Source ON Resistance
 - $R_{DS(ON)} = 0.68\Omega$ (Typ.)
- High Forward Transfer Admittance
 - $|Y_{fs}| = 0.5S$ (Typ.)
- Low Leakage Current
 - $I_{DSS} = -100\mu A$ (Max.) @ $V_{DS} = -60V$
- Enhancement-Mode
 - $V_{th} = -0.8 \sim -2.0V$ @ $V_{DS} = -10V$, $I_D = -1mA$

Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	-60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	A
	Pulse	I_{DP}	
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	0.5	W
Drain Power Dissipation *	P_D^*	1.5	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

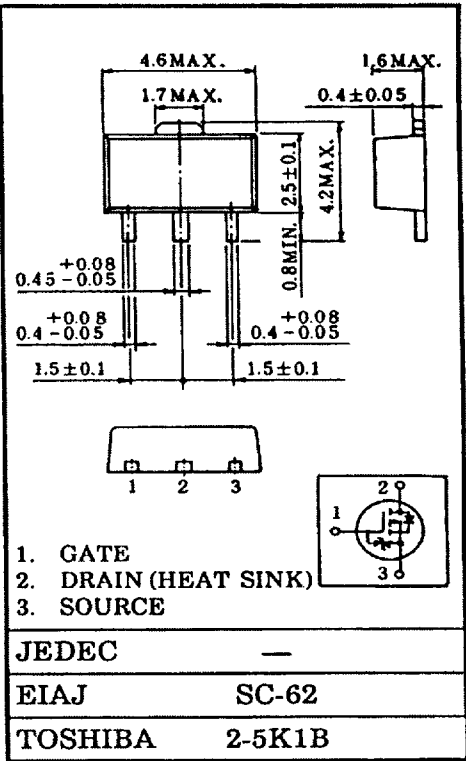
P_D^* : Mounted on ceramic substrate (600 mm² x 0.8t)

Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	250	$^\circ C/W$

This transistor is an electrostatic sensitive device. Please handle with care.

Unit in mm

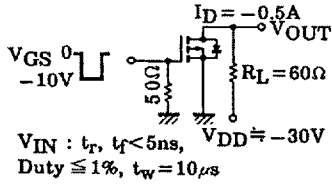


Weight : 0.05g

Marking



Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	—	—	-100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = -10mA, V_{GS} = 0V$	-60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10V, I_D = -1mA$	-0.8	—	-2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = -4V, I_{DS} = -0.5A$	—	1.0	1.40	Ω
			$V_{GS} = 10V, I_{DS} = -0.5A$	—	0.68	0.85	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10V, I_{DS} = -0.5A$	0.3	0.5	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1MHz$	—	150	220	pF
Reverse Transfer Capacitance		C_{rss}		—	20	40	
Output Capacitance		C_{oss}		—	75	120	
Switching Time	Rise Time	t_r	 $I_D = -0.5A$ $V_{GS} = 0V, -10V$ 50Ω 50Ω $R_L = 60\Omega$ $V_{IN} : t_r, t_f < 5ns, V_{DD} = -30V$ $Duty \leq 1\%, t_w = 10\mu s$	—	60	120	ns
	Turn-on Time	t_{on}		—	90	180	
	Fall Time	t_f		—	40	80	
	Turn-off Time	t_{off}		—	80	160	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = -48V, V_{GS} = -10V,$ $I_D = -1A$	—	6.5	13	nC
Gate-Source Charge		Q_{gs}		—	4.2	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	2.3	—	

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	-1	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	-3	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -1A, V_{GS} = 0V$	—	—	1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = -1A, V_{GS} = 0V$	—	50	—	ns
Reverse Recovered Charge	Q_{rr}	$dI_{DR}/dt = 50A/\mu s$	—	55	—	μC

